



A dry etching system specializing in the processing of chemical compounds and non-volatile materials

APX300 Dry Etcher (S Option)

The APX300 (S option) is a dry etching system specializing in the processing of chemical compounds and non-volatile materials. It is compatible with wafers of 2 inches to 8 inches and irregular substrates, and two transport methods can be selected: "Atmospheric loading supply" and "Vacuum load lock supply" CE certificated. This equipment is a single-wafer processing type for wafers of 8 inches or smaller, and can be selected and optimized for a wide range of process applications such as power semiconductors, optical communications, high-frequency communications, RF modules, and MEMS. In addition, as a post-etching process, the ashing and rinsing chambers can be expanded according to the process application.

Key Features

Two types of plasma sources enable high-speed and high-precision machining. Achieves high-speed deep drilling of compound materials (substrate penetration, etc.) and control of processed film thickness.

Achieves metal machining without residue and corrosion by adding usher and rinse chambers.

In-situ garment removal function with top plate enables stable machining of non-volatile materials.



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<https://ap.connect.panasonic.com/th/en/apx300-dry-etchers-option>

Dimensions (mm)	<p>【Load lock wafer Handling】 W 1 350 mm × D 2 230 mm × H 2 000 mm (Exclude touch panel , operation section and signal tower)</p> <p>【Atmospheric loading supply】 W 1 375 mm × D 2 600 mm × H 2 000 mm (Exclude touch panel , operation section and signal tower)</p>
Plasma source	ICP Plasma
Model-No. (Model Name)	NM-EFE3AA-S
Process gas	Standard 4 lines (Maximum 6 Lines : Chlorinated Gas , Fluoride Gas , Ar , O ₂ , He , etc.)
Wafer size	φ100 mm / 150 mm wafer with orientation flat φ200 mm wafer with notch* ¹
Mass (Weight)	2 000 kg (Di ers depending on machine configuration)
Power Source	3-phase AC 200 / 208 / 220 / 230 / 240 ±10 V , 50 / 60 Hz , 21.00 kVA* ²
Pneumatic Source	0.5 MPa to 0.7 MPa , 250 L / min (A.N.R.)
N₂ Source	0.1 MPa to 0.2 MPa , 50 L / min (A.N.R.)
Footnote Description	<p>Please refer to the specifications on details.</p> <ol style="list-style-type: none"> 1. For other wafer sizes , please contact us. 2. 3-phase electricity has two kinds of lineage. Figure shows total.